

Silicon PNP Power Transistors

2SA738

DESCRIPTION

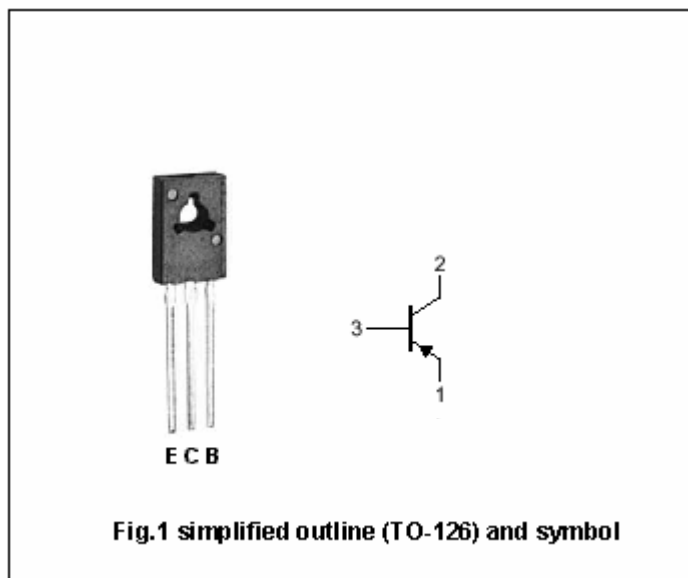
- With TO-126 package
- High current
- Complement to type 2SC1368

APPLICATIONS

- Driver stages in high-fidelity amplifiers and television circuits

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-25	V
V_{CEO}	Collector-emitter voltage	Open base	-25	V
V_{EBO}	Emitter -base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_{CM}	Collector current-Peak		-2.0	A
P_t	Total power dissipation	$T_C=25^\circ\text{C}$	8	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA; I_B=0$	-25			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-0.5A; I_B=-50mA$			-0.5	V
V_{BE}	Base-emitter voltage	$I_C=-500mA; V_{CE}=-2V$			-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-25V; I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-1.0	μA
h_{FE-1}	DC current gain	$I_C=-150mA; V_{CE}=-2V$	35		320	
h_{FE-2}	DC current gain	$I_C=-500mA; V_{CE}=-2V$	25			
f_T	Transition frequency	$I_C=-50mA; V_{CE}=-5V$		160		MHz

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PACKAGE OUTLINE

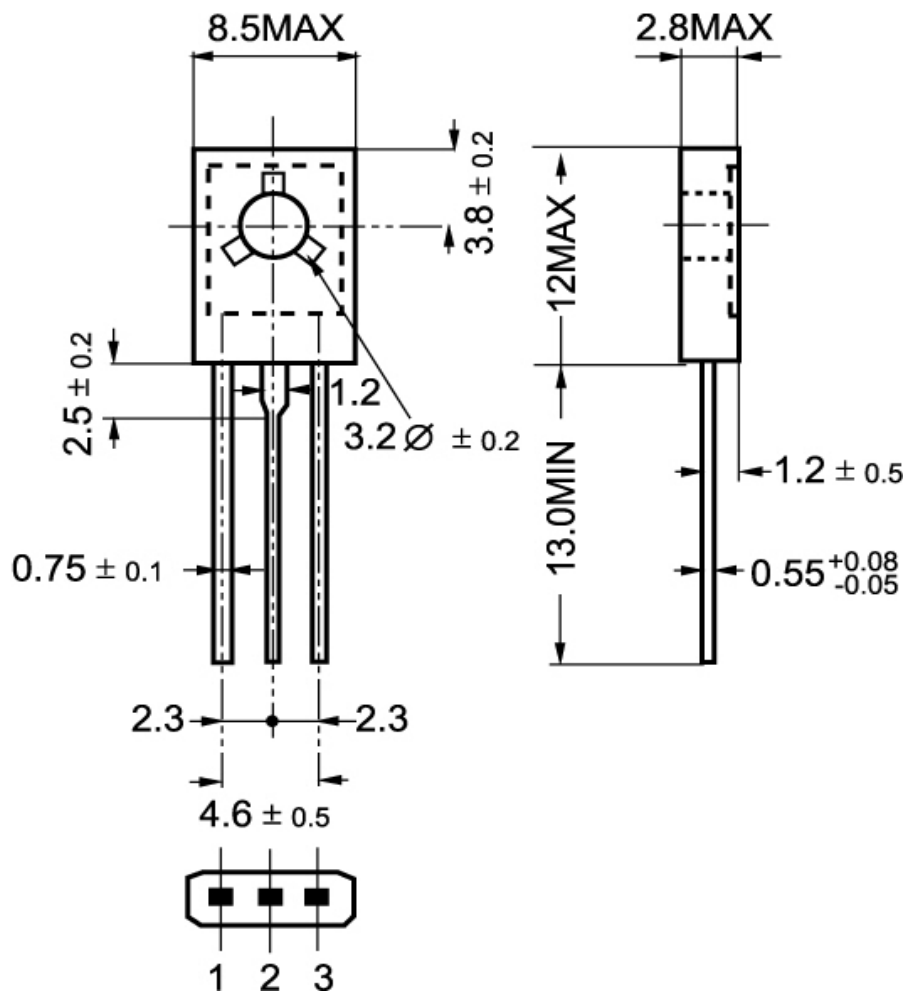


Fig.2 Outline dimensions